

**TRANSISTOR (PNP)**
**Plastic-Encapsulate Transistor**
**FEATURES**

Power dissipation

$$P_{CM} : 0.2W \text{ (Tamb=25}^\circ\text{C)}$$

Collector current

$$I_{CM} : -0.15A$$

Collector-base Voltage

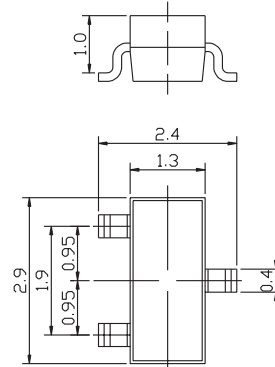
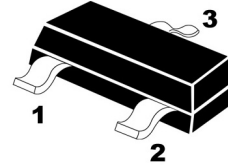
$$V_{(BR)CBO} : -50 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^\circ\text{C to } +150^\circ\text{C}$$

**MARKING: A1015LT1=BA**
**SOT-23**

1. BASE
2. EMITTER
3. COLLECTOR



Unit:mm

**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Ratings at 25°C ambient temperature unless otherwise specified.

**ELECTRICAL CHARACTERISTICS**

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-50		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -0.1mA, I_B = 0$	-50		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$		-0.1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -6V, I_C = -2mA$	130	400	
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C = -100mA, I_B = -10mA$		-0.3	V
Base-emitter saturation voltage	$V_{BEsat}$	$I_C = -100mA, I_B = -10mA$		-1.1	V
Base-emitter voltage	$V_{BEF}$	$I_E = -310mA$		-1.45	V
Transition frequency	$f_r$	$V_{CE} = -10V, I_C = -1mA, f = 30MHz$	80		MHz

**CLASSIFICATION OF  $h_{FE}$** 

Rank	L	H
Range	130-200	200-400

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